

## Continental Device India Limited





#### **SOT-23 Formed SMD Package**

#### BCX70G BCX70H BCX70J BCX70K

### SILICON PLANAR EPITAXIAL TRANSISTORS

N-P-N silicon transistors

#### Marking

BCX70G = AG

BCX70H = AH

BCX70J = AJ

BCX70K = AK

#### Pin configuration

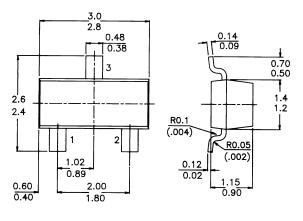
1 = BASE

2 = EMITTER

3 = COLLECTOR



# PACKAGE OUTLINE DETAILS ALL DIMENSIONS IN mm



#### ABSOLUTE MAXIMUM RATINGS

Collector-emitter voltage ( $V_{BE} = 0$ )	$V_{C\!E\!S}$	max.	45 V
Collector-emitter voltage (open base)	$V_{CE0}$	max.	45 V
Collector current (d.c.)	$I_C$	max.	200 mA
Total power dissipation at $T_{amb} = 25$ °C	$P_{tot}$	max.	<i>250</i> mW
Junction temperature	$T_{j}$	max.	150 ° C
Transition frequency at $f = 100 \text{ MHz}$	3		
$V_{CE} = 5 V$ ; $I_C = 10 mA$	$f_T$	typ.	250 MHz
Noise figure at f: 1 kHz			
$V_{CE} = 5 V$ ; $I_{C:} 200 \text{ mA}$ ; $B = 200 \text{ Hz}$	F	typ.	2 dB
<b>RATINGS</b> (at $T_A = 25^{\circ}C$ unless otherwise specified)			

Limiting values

Collector-emitter voltage $(V_{BE} = 0)$	$V_{C\!E\!S}$	max.	45 V
Collector-emitter voltage (open base)	$V_{CE0}$	max.	45 V
Emitter-base voltage (open collector)	$V_{FR0}$	max.	5 V

### BCX70G BCX70H BCX70J BCX70K

Collector current (d.c.)  Base current  Total power dissipation up to T <sub>amb</sub> = 2	25 °C			I <sub>C</sub> l <sub>B</sub> P <sub>tot</sub>	max. max. max.	<i>50</i>	mA mA mW
Storage temperature  Junction temperature				T <sub>stg</sub> T <sub>j</sub>	-55 to max.	+15	
THERMAL RESISTANCE							
From junction to ambient				$R_{th\ j-a}$	=	<i>500</i>	KW
CHARACTERISTICS							
T <sub>amb:</sub> 25 °C unless otherwise specified							
Collector-emitter cut-off current				_			
$V_{BE} = 0$ ; $V_{CE} = 45 \text{ V}$	0 <i>C</i>			$I_{CES}$	<		nA
$V_{BE} = 0$ ; $V_{CE} = 45$ V; $T_{amb} = 150$	C			$I_{CES}$	<	20	mA
Emitter-base cut-off current $I_C = 0$ ; $V_{EB} = 4 V$				$I_{EB0}$	<	20	nΑ
Saturation voltages				<sup>1</sup> EB0		20	ш
at $I_C = 10 \text{ mA}$ ; $I_B = 0.25 \text{ mA}$				VCEsat	0,05 to	0.35	V
20 2C 20 22 25 25 25 25 25 25 25 25 25 25 25 25				V <sub>BEsat</sub>			
at $I_C = 50 \text{ mA}$ ; $I_B = 1,25 \text{ mA}$				$V_{CEsat}$			
at 10 00 112 1, 1 <sub>B</sub> 1,20 112 1				V <sub>BEsat</sub>	0,7 to		
Transition frequency at $f = 100 \text{ MHz} \text{ D}$				· DLSat	>	125	
$I_C = 10 \text{ mA}; V_{CE} = 5 \text{ V}$				$f_T$	typ.	250	MHz
Collector capacitance at $f = 1$ MHz							
$I_E = I_e = 0; \ V_{CB} = 10 \ V$				$C_c$	typ.	2,5	рF
Emitter capacitance at $f = 1$ MHz							
$I_C = I_c = 0; V_{EB} = 0.5 V$				$C_{e}$	typ.		pF
Noise figure at $R_S = 2 \text{ kW}$ ,	D 000			п	typ.		dB
$I_C = 200 \text{ mA}; \ V_{CE} = 5 \ V; \ f = 1 \ \text{kHz};$	B = 200	HZ		F	<	ь	dВ
			BCX70G	70H	70J	70K	
D.C. current gain $V_{CE} = 5V; IC = 10 \text{mA}$	$h_{FE}$	>		40	30	100	
$V_{CE} = 5V$ , $I_{C} = 1001A$ $V_{CE} = 5V$ ; $I_{C} = 2 \text{ mA}$	$h_{FE}$	>	120	180	250	380	
CE VIIII	-TE	<	220	310	460	630	
$V_{CE} = 1 \ V; I_{C} = 50 \ mA$	$h_{FE}$	>	50	70	90	100	
Small-signal current gain							
$V_{CE} = 5 \text{ V}; IC = 2 \text{ mA}; f = 1 \text{ kHz}$	hfe	>	125	175	250	350	
$V_{CE} = 0$ V, $I_{C} = 2$ Hz I, $I = 1$ Hz IZ	me	<	250	350	500	700	
Output admittance							
$V_{CE} = 5 V$ ; $IC = 2 mA$ ; $f = 1 kHz$ Base-emitter voltage	hoe	typ.	18	24	30	50	
$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}$	$V_{BE}$			0,5	55 to 0.7	75	V
. 01 0 1, 20 2 222 2	· DE	typ.			0,65		V
$V_{CE} = 5 \ V; I_{C} = 10 \ \text{mA}$	$V_{BE}$	typ.			0,52		V
$V_{CE} = 1 \ V; I_C = 50 \ mA$	$V_{BE}$	typ.			0,78		V

#### **Notes**

#### **Disclaimer**

The product information and the selection guides facilitate selection of the CDIL's Discrete Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished on the CDIL Web Site/CD is believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Discrete Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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C-120 Naraina Industrial Area, New Delhi 110 028, India.

Telephone + 91-11-579 6150 Fax + 91-11-579 9569, 579 5290
e-mail sales@cdil.com www.cdil.com